

GTT2610**N-CHANNEL ENHANCEMENT MODE POWER MOSFET**

BVDSS	60V
RDS(ON)	90mΩ
ID	3A

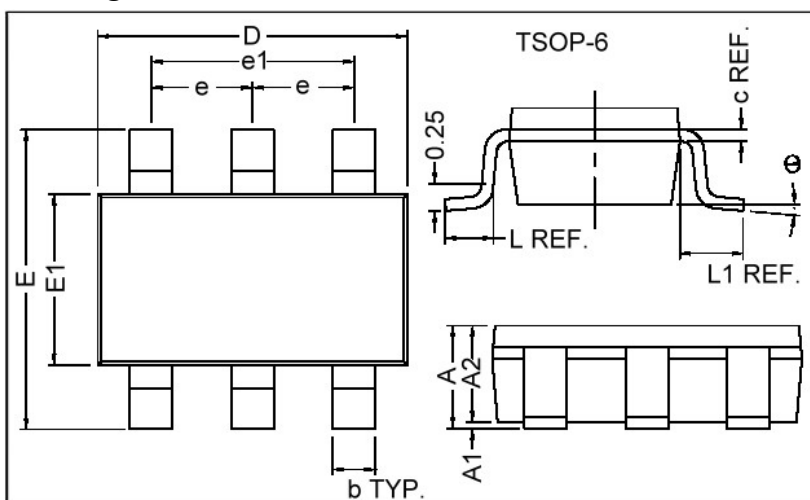
Description

The GTT2610 utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

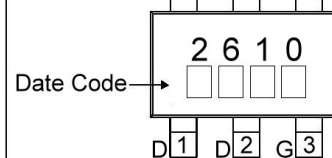
The GTT2610 is universally used for all commercial-industrial applications.

Features

- *Simple Drive Requirement
- *Small Package Outline

Package Dimensions

Marking : D 6 D 5 S 4



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.10	MAX.	L	0.45	REF.
A1	0	0.10	L1	0.60	REF.
A2	0.70	1.00	θ	0°	10°
c	0.12	REF.	b	0.30	0.50
D	2.70	3.10	e	0.95	REF.
E	2.60	3.00	e1	1.90	REF.
E1	1.40	1.80			

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ³ , $V_{GS}@4.5V$	$I_D @TA=25^{\circ}C$	3.0	A
Continuous Drain Current ³ , $V_{GS}@4.5V$	$I_D @TA=70^{\circ}C$	2.3	A
Pulsed Drain Current ^{1,2}	I_{DM}	10	A
Power Dissipation	$P_D @TA=25^{\circ}C$	2	W
Linear Derating Factor		0.016	W/°C
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	°C

Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-ambient ³ Max.	R_{thj-a}	62.5	°C/W

Electrical Characteristics (T_j = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	V _{GS} =0, I _D =250uA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.05	-	V/°C	Reference to 25°C, I _D =1mA
Gate Threshold Voltage	V _{GS(th)}	1.0	-	3.0	V	V _{DS} =V _{GS} , I _D =250uA
Forward Transconductance	g _{fs}	-	5.0	-	S	V _{DS} =5V, I _D =3A
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	10	uA	V _{DS} =60V, V _{GS} =0
Drain-Source Leakage Current(T _j =70°C)		-	-	25	uA	V _{DS} =48V, V _{GS} =0
Static Drain-Source On-Resistance	R _{DS(ON)}	-	-	90	mΩ	V _{GS} =10V, I _D =3A
		-	-	120		V _{GS} =4.5V, I _D =2A
Total Gate Charge ²	Q _g	-	6	10	nC	I _D =3A V _{DS} =48V V _{GS} =4.5V
Gate-Source Charge	Q _{gs}	-	1.6	-		
Gate-Drain ("Miller") Charge	Q _{gd}	-	3	-		
Turn-on Delay Time ²	T _{d(on)}	-	6	-	ns	V _{DS} =30V I _D =1A V _{GS} =10V R _G =3.3Ω R _D =30Ω
Rise Time	T _r	-	5	-		
Turn-off Delay Time	T _{d(off)}	-	16	-		
Fall Time	T _f	-	3	-		
Input Capacitance	C _{iss}	-	490	780	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	-	55	-		
Reverse Transfer Capacitance	C _{rss}	-	40	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	1.2	V	I _S =1.2A, V _{GS} =0V
Reverse Recovery Time	T _{rr}	-	25	-	ns	I _S =3A, V _{GS} =0V dI/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	26	-	nC	

Notes: 1. Pulse width limited by Max. junction temperature.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

3. Surface mounted on 1 in² copper pad of FR4 board;156°C/W when mounted on min. copper pad.

Characteristics Curve

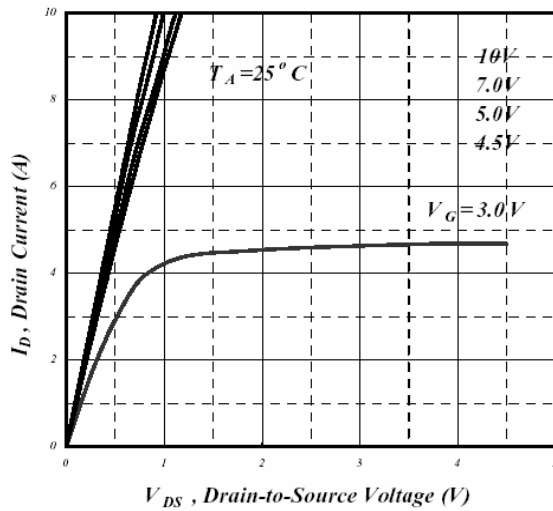


Fig 1. Typical Output Characteristics

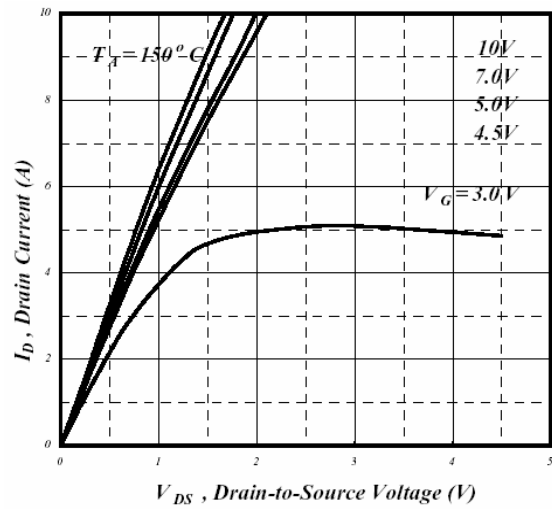


Fig 2. Typical Output Characteristics

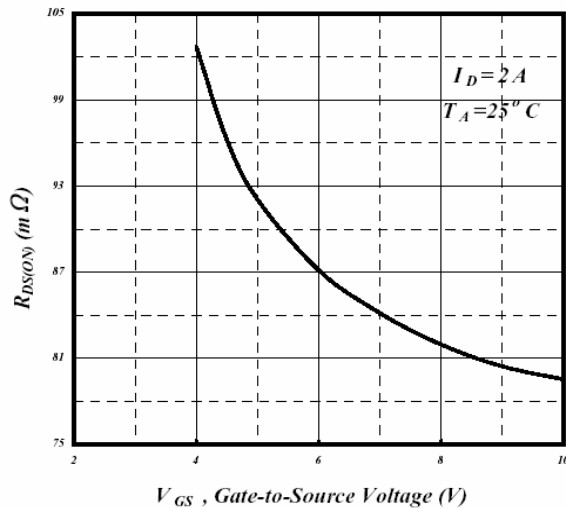


Fig 3. On-Resistance v.s. Gate Voltage

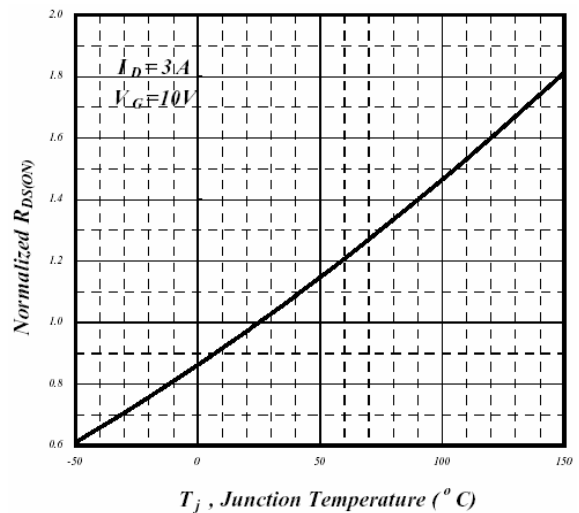


Fig 4. Normalized On-Resistance v.s. Junction Temperature

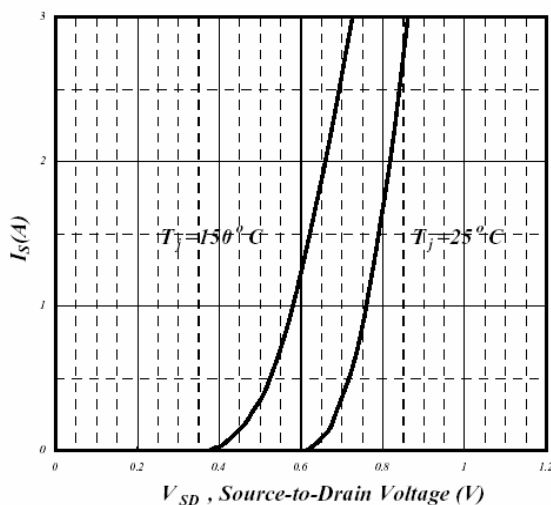


Fig 5. Forward Characteristics of Reverse Diode

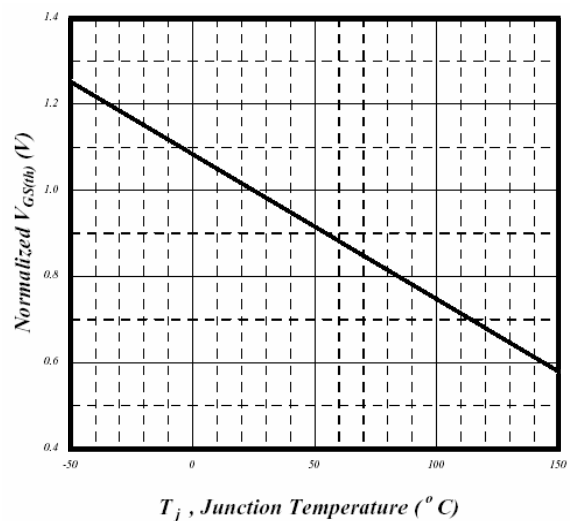


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

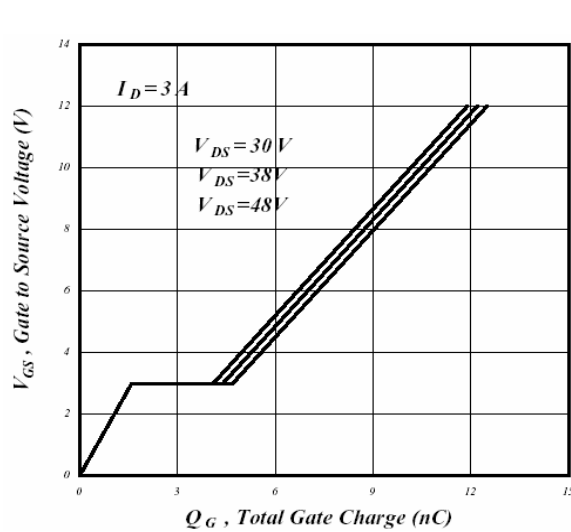


Fig 7. Gate Charge Characteristics

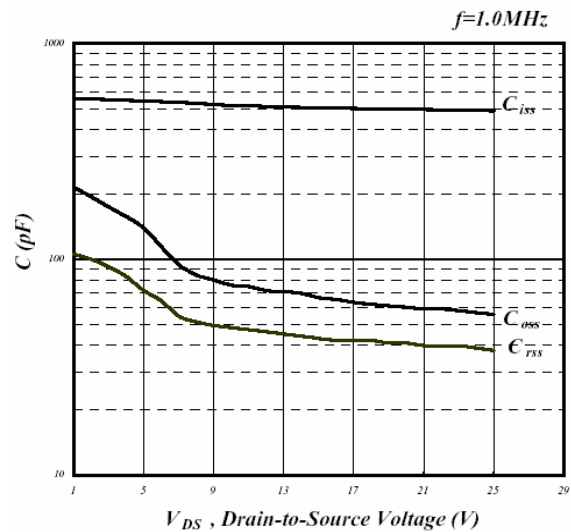


Fig 8. Typical Capacitance Characteristics

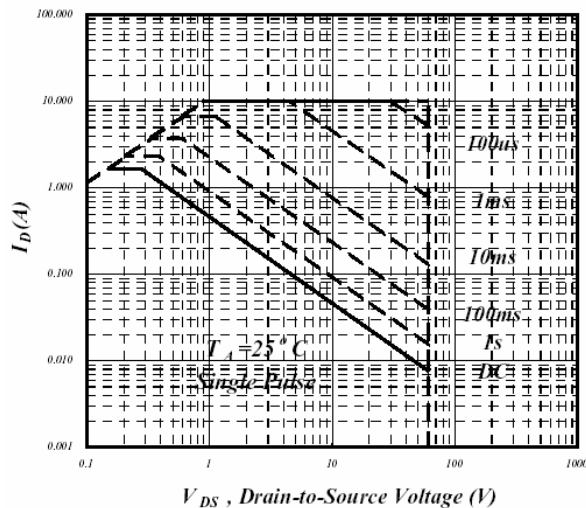


Fig 9. Maximum Safe Operating Area

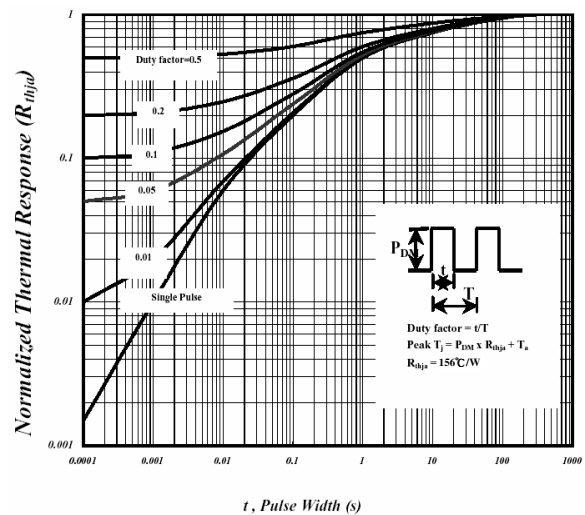


Fig 10. Effective Transient Thermal Impedance

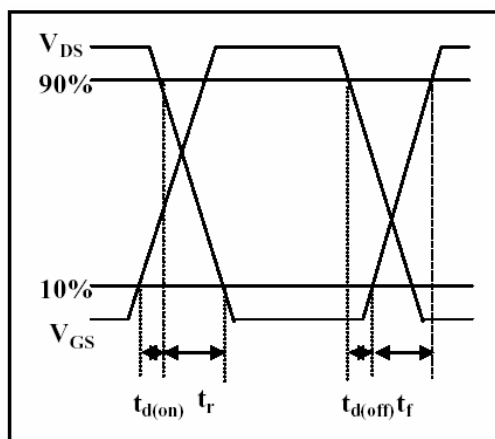


Fig 11. Switching Time Waveform

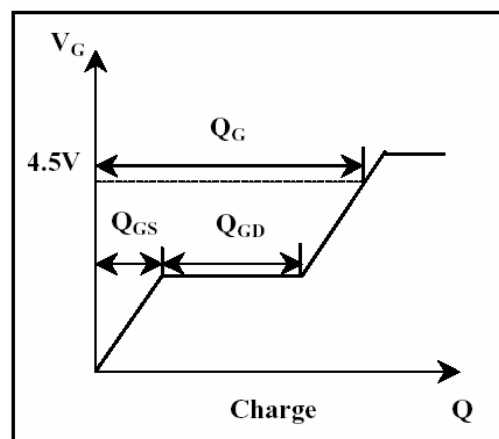


Fig 12. Gate Charge Waveform

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of GTM.
- GTM reserves the right to make changes to its products without notice.
- GTM semiconductor products are not warranted to be suitable for use in life-support Applications, or systems.
- GTM assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165